					Docket Number (Optional)		Application Number						
INFORMATION DISCLOSURE CITATION					YOR920030500US1 Applicant(s)		10/697,271						
(Use several sheets if negessary)					Newns, et al.								
	JAN 2 9 2004 2			Filing Date			Group Art Unit						
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/GH/		6,515,957 B1	02/04/03	Newns, et al.									
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